

| L Number | Hits | Search Text   | DB  | Time stamp       |
|----------|------|---|---|------------------|
| 84       | 274  | DFB and (semiconductor near laser) and active and clad\$5 and grating and insulat\$4 and electrode  | USPAT;<br>US-PGPUB                                      | 2003/05/02 17:08 |
| 87       | 32   | DFB and (semiconductor near laser) and active and clad\$5 and grating and (insulat\$4 with gap) and electrode   | USPAT;<br>US-PGPUB                                      | 2003/05/02 17:09 |
| 90       | 28   | DFB and (semiconductor near laser) and active and clad\$5 and grating and (insulat\$4 with gap) and electrode   | USPAT   | 2003/05/02 17:36 |
| 91       | 25   | DFB and (semiconductor near laser) and active and clad\$5 and grating and (insulat\$4 with gap) and electrode and contact   | USPAT   | 2003/05/02 18:14 |
| 92       | 3    | DFB and (semiconductor near laser) and active and clad\$5 and (grating with InGaAs) and (insulat\$4 with gap) and electrode and contact   | USPAT   | 2003/05/02 18:24 |
| 93       | 8    | DFB and (semiconductor near laser) and (grating near3 InGaAs)   | USPAT   | 2003/05/02 18:25 |
| -        | 235  | (semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/10/31 14:04 |
| -        | 172  | ((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 09:07 |
| -        | 7    | ((semiconductor near laser) and (substrate near (layer or medium or film or region)) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near (layer or medium or film or region)) and (groove or grind or pace or rut\$ or rote) and (clad\$ near (layer or medium or film or region))) and 372/\$  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 09:18 |
| -        | 86   | ((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$ and (waveguide near (layer or film or medium or region))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 11:31 |
| -        | 4    | ((semiconductor near laser) and (substrate near (layer or medium or film or region)) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near (layer or medium or film or region)) and (groove or grind or pace or rut\$ or rote) and (clad\$ near (layer or medium or film or region))) and 372/\$ and (waveguide near (layer or film or medium or region)) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 09:17 |
| -        | 47   | ((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$ and (waveguide near (layer or film or medium or region))) and 372/96   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 09:26 |
| -        | 4    | (semiconductor near laser) and (substrate near layer) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near layer) and (groove) and (clad\$ near layer) and 372/\$ and (waveguide near (layer or film or medium or region))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 09:29 |

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|---|----|---|---|------------------|
| - | 4  | (semiconductor near laser) and (substrate near layer) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near layer) and (groove) and (clad\$ near layer) and 372/\$ and (waveguide near layer)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 09:35 |
| - | 40 | ((((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$ and (waveguide near (layer or film or medium or region))) and 372/96) and (waveguide near layer)               | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 09:38 |
| - | 8  | (semiconductor near laser) and substrate and (grating same (insulat\$ or nonconductor or non adj conductor or isolat\$) with (groove or grind or pace or rut\$ or rote)) and electrode and clad\$ and 372/\$ and (waveguide near (layer or film or medium or region)) and 372/96 and (waveguide near layer)                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 15:51 |
| - | 6  | ((semiconductor near laser) and substrate and (grating same (insulat\$ or nonconductor or non adj conductor or isolat\$) with (groove or grind or pace or rut\$ or rote)) and electrode and clad\$ and 372/\$ and (waveguide near (layer or film or medium or region)) and 372/96 and (waveguide near layer)) and resonator | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2001/11/01 13:26 |
| - | 2  | (semiconductor near laser) and substrate and (grating same (insulat\$ or nonconductor or non adj conductor or isolat\$) with (groove or grind or pace or rut\$ or rote) same resonator) and electrode and clad\$ and 372/\$ and (waveguide near (layer or film or medium or region)) and 372/96 and (waveguide near layer)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/05/02 17:07 |